

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) An InP substrate for epitaxial growth,  
wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source, the light source having a wavelength of 488 nm, every portion of an effectively used area measured by Surfscan 6220 exhibits a haze of not more than 1 ppm, the InP substrate having a size of at least two inches; and  
wherein the InP substrate comprises  
~~the haze is not more than 1 ppm all over an effectively used area of the InP substrate and~~  
an off-angle with respect to a plane direction ~~[[is]]~~ of 0.05 to 0.10°, ~~wherein the~~  
~~effectively used area includes the surface area of the substrate, with the exception of the~~  
~~peripheral part including the chamfered part of the substrate.~~

2. (Cancelled)

3. (Cancelled)

4. (Previously Presented) The InP substrate as claimed in claim 1, wherein a dislocation density is not more than 1000/cm<sup>2</sup>.

5. (Previously Presented) The InP substrate as claimed in claim 4, wherein the dislocation density is not more than 500/cm<sup>2</sup>.

6. (Previously Presented) A compound semiconductor substrate for epitaxial growth, comprising an InP substrate and at least one epitaxial layer on the InP substrate, wherein:

the InP substrate has an off-angle with respect to a plane direction of  $0.05$  to  $0.10^\circ$ ,

the InP substrate has a haze of  $0.5$  to  $0.8$  ppm, and

the haze in a surface of the at least one epitaxial layer is not more than  $1$  ppm,

wherein haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto the surface of the at least one epitaxial layer or a surface of the InP substrate, by intensity of the incident light from the light source.

7. (Previously Presented) An InP substrate for epitaxial growth,

wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source,

the haze is not more than  $1$  ppm all over an effectively used area of the InP substrate, and

an off-angle with respect to a plane direction is  $0.05$  to  $0.10^\circ$ .

8. (New) An InP substrate for epitaxial growth,

wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source, the light source having a

wavelength of 488 nm, every portion of an effectively used area of the substrate exhibits a haze of not more than 1 ppm,

wherein the InP substrate has a size of at least two inches, and comprises an off-angle with respect to a plane direction of 0.05 to 0.10°.